TEXAS INSTRUMENTS

Data sheet acquired from Harris Semiconductor
SCHS188B

January 1998 - Revised May 2003

CD54/74HC534, CD54/74HCT534, CD54/74HC564, CD54/74HCT564

High-Speed CMOS Logic Octal D-Type Flip-Flop, Three-State Inverting Positive-Edge Triggered

Features

- **Buffered Inputs**
- **Common Three-State Output-Enable Control**
- **Three-State Outputs**
- **Bus Line Driving Capability**
- **Typical Propagation Delay = 13ns at V_{CC} = 5V, C_L = 15pF, T_A = 25°C (Clock to Output)**
- **Fanout (Over Temperature Range)**
  - **Standard Outputs . . . . 10 LSTTL Loads**
  - **Bus Driver Outputs . . . . 15 LSTTL Loads**
- **Wide Operating Temperature Range . . . -55°C to 125°C**
- **Balanced Propagation Delay and Transition Times**
- **Significant Power Reduction Compared to LSTTL Logic ICs**
- **HC Types**
  - **2V to 6V Operation**
  - **High Noise Immunity: N_{IL} = 30%, N_{IH} = 30% of V_{CC} at V_{CC} = 5V**
- **HCT Types**
  - **4.5V to 5.5V Operation**
  - **Direct LSTTL Input Logic Compatibility, V_{IL}= 0.8V (Max), V_{IH} = 2V (Min)**
  - **CMOS Input Compatibility, $I_I \leq 1\mu A$ at V_{OL}, V_{OH}**

Description

The ’HC534, ’HCT534, ’HC564, and ’HCT564 are high speed Octal D-Type Flip-Flops manufactured with silicon gate CMOS technology. They possess the low power consumption of standard CMOS integrated circuits, as well as the ability to drive 15 LSTTL loads. Due to the large output drive capability and the three-state feature, these devices are ideally suited for interfacing with bus lines in a bus organized system. The two types are functionally identical and differ only in their pinout arrangements.

The ’HC534, ’HCT534, ’HC564, and ’HCT564 are positive edge triggered flip-flops. Data at the D inputs, meeting the setup and hold time requirements, are inverted and transferred to the Q outputs on the positive going transition of the CLOCK input. When a high logic level is applied to the OUTPUT ENABLE input, all outputs go to a high impedance state, regardless of what signals are present at the other inputs and the state of the storage elements.

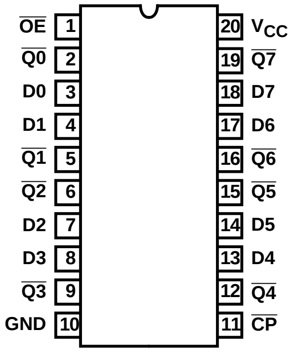
The HCT logic family is speed, function, and pin compatible with the standard LS logic family.

Ordering Information

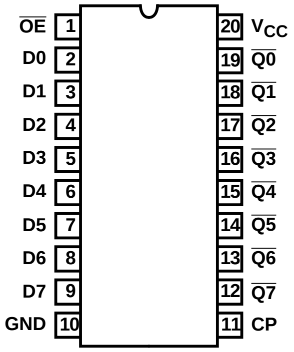
PART NUMBER	TEMP. RANGE (°C)	PACKAGE
CD54HC534F3A	-55 to 125	20 Ld CERDIP
CD54HC564F3A	-55 to 125	20 Ld CERDIP
CD54HCT534F3A	-55 to 125	20 Ld CERDIP
CD54HCT564F3A	-55 to 125	20 Ld CERDIP
CD74HC534E	-55 to 125	20 Ld PDIP
CD74HC564E	-55 to 125	20 Ld PDIP
CD74HC564M	-55 to 125	20 Ld SOIC
CD74HCT534E	-55 to 125	20 Ld PDIP
CD74HCT564E	-55 to 125	20 Ld PDIP
CD74HCT564M	-55 to 125	20 Ld SOIC

Pinouts

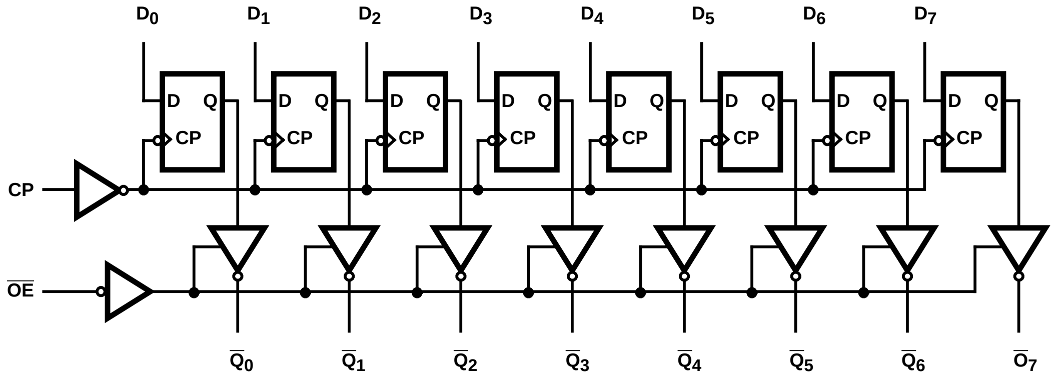
CD54HC534, CD54HCT534
(CERDIP)
CD74HC534, CD74HCT534
(PDIP)
TOP VIEW



CD54HC564, CD54HCT564
(CERDIP)
CD74HC564, CD74HCT564
(PDIP, SOIC)
TOP VIEW



Functional Diagram



TRUTH TABLE

INPUTS			OUTPUT
$\overline{OE}$	CP	Dn	$\overline{Qn}$
L	↑	H	L
L	↑	L	H
L	L	X	No Change
H	X	X	Z

H = High Level (Steady State)
L = Low Level (Steady State)
X= Don't Care
↑= Transition from Low to High Level
Z = High Impedance State

Absolute Maximum Ratings

DC Supply Voltage, V_{CC} . . . . -0.5V to 7V
DC Input Diode Current, I_{IK}
  For $V_I < -0.5V$ or $V_I > V_{CC} + 0.5V$ . . . . ±20mA
DC Output Diode Current, I_{OK}
  For $V_O < -0.5V$ or $V_O > V_{CC} + 0.5V$ . . . . ±20mA
DC Drain Current, per Output, I_O
  For $-0.5V < V_O < V_{CC} + 0.5V$ . . . . ±35mA
DC Output Source or Sink Current per Output Pin, I_O
  For $V_O > -0.5V$ or $V_O < V_{CC} + 0.5V$ . . . . ±25mA
DC V_{CC} or Ground Current, I_{CC} . . . . ±50mA

Thermal Information

Thermal Resistance (Typical, Note 1)	θ_{JA} (°C/W)
E (PDIP) Package	69
M (SOIC) Package	58

Maximum Junction Temperature . . . . 150°C
Maximum Storage Temperature Range . . . . -65°C to 150°C
Maximum Lead Temperature (Soldering 10s) . . . . 300°C
  (SOIC - Lead Tips Only)

Operating Conditions

Temperature Range, T_A . . . . -55°C to 125°C
Supply Voltage Range, V_{CC}
  HC Types . . . . 2V to 6V
  HCT Types . . . . 4.5V to 5.5V
DC Input or Output Voltage, V_I, V_O . . . . 0V to V_{CC}
Input Rise and Fall Time
  2V . . . . 1000ns (Max)
  4.5V . . . . 500ns (Max)
  6V . . . . 400ns (Max)

CAUTION: Stresses above those listed in "Absolute Maximum Ratings" may cause permanent damage to the device. This is a stress only rating and operation of the device at these or any other conditions above those indicated in the operational sections of this specification is not implied.

NOTE:

1. The package impedance is calculated in accordance with JESD 51-7.

DC Electrical Specifications

		TEST CONDITIONS			25°C			-40°C TO 85°C		-55°C TO 125°C		
PARAMETER	**SYMBOL**	**V_I (V)**	**I_O (mA)**	**V_{CC} (V)**	**MIN**	**TYP**	**MAX**	**MIN**	**MAX**	**MIN**	**MAX**	**UNITS**
HC TYPES												
High Level Input Voltage	V_{IH}	-	-	2	1.5	-	-	1.5	-	1.5	-	V
				4.5	3.15	-	-	3.15	-	3.15	-	V
				6	4.2	-	-	4.2	-	4.2	-	V
Low Level Input Voltage	V_{IL}	-	-	2	-	-	0.5	-	0.5	-	0.5	V
				4.5	-	-	1.35	-	1.35	-	1.35	V
				6	-	-	1.8	-	1.8	-	1.8	V
High Level Output Voltage CMOS Loads	V_{OH}	V_{IH} or V_{IL}	-0.02	2	1.9	-	-	1.9	-	1.9	-	V
			-0.02	4.5	4.4	-	-	4.4	-	4.4	-	V
			-0.02	6	5.9	-	-	5.9	-	5.9	-	V
High Level Output Voltage TTL Loads			-	-	-	-	-	-	-	-	-	V
			-6	4.5	3.98	-	-	3.84	-	3.7	-	V
			-7.8	6	5.48	-	-	5.34	-	5.2	-	V
Low Level Output Voltage CMOS Loads	V_{OL}	V_{IH} or V_{IL}	0.02	2	-	-	0.1	-	0.1	-	0.1	V
			0.02	4.5	-	-	0.1	-	0.1	-	0.1	V
			0.02	6	-	-	0.1	-	0.1	-	0.1	V
Low Level Output Voltage TTL Loads			-	-	-	-	-	-	-	-	-	V
			6	4.5	-	-	0.26	-	0.33	-	0.4	V
			7.8	6	-	-	0.26	-	0.33	-	0.4	V
Input Leakage Current	I_I	V_{CC} or GND	-	6	-	-	±0.1	-	±1	-	±1	µA

DC Electrical Specifications (Continued)

PARAMETER	SYMBOL	TEST CONDITIONS		V_{CC} (V)	25°C			-40°C TO 85°C		-55°C TO 125°C		UNITS
		V_I (V)	I_O (mA)		MIN	TYP	MAX	MIN	MAX	MIN	MAX	
Quiescent Device Current	I_{CC}	V_{CC} or GND	0	6	-	-	8	-	80	-	160	μA
Three- State Leakage Current	V_{IL} or V_{IH}	$V_O = V_{CC}$ or GND	-	6	-	-	±0.5	-	±5.0	-	±10	μA
HCT TYPES												
High Level Input Voltage	V_{IH}	-	-	4.5 to 5.5	2	-	-	2	-	2	-	V
Low Level Input Voltage	V_{IL}	-	-	4.5 to 5.5	-	-	0.8	-	0.8	-	0.8	V
High Level Output Voltage CMOS Loads	V_{OH}	V_{IH} or V_{IL}	-0.02	4.5	4.4	-	-	4.4	-	4.4	-	V
High Level Output Voltage TTL Loads			-6	4.5	3.98	-	-	3.84	-	3.7	-	V
Low Level Output Voltage CMOS Loads	V_{OL}	V_{IH} or V_{IL}	0.02	4.5	-	-	0.1	-	0.1	-	0.1	V
Low Level Output Voltage TTL Loads			6	4.5	-	-	0.26	-	0.33	-	0.4	V
Input Leakage Current	I_I	V_{CC} and GND	0	5.5	-		±0.1	-	±1	-	±1	μA
Quiescent Device Current	I_{CC}	V_{CC} or GND	0	5.5	-	-	8	-	80	-	160	μA
Three- State Leakage Current	V_{IL} or V_{IH}	$V_O = V_{CC}$ or GND	-	5.5	-	-	±0.5	-	±5.0	-	±10	μA
Additional Quiescent Device Current Per Input Pin: 1 Unit Load	ΔI_{CC} (Note 2)	V_{CC} -2.1	-	4.5 to 5.5	-	100	360	-	450	-	490	μA

NOTE:

2. For dual-supply systems theoretical worst case (V_I = 2.4V, V_{CC} = 5.5V) specification is 1.8mA.

HCT Input Loading Table

INPUT	UNIT LOADS
D0 - D7	0.15
CP	0.30
$\overline{\text{OE}}$	0.55

NOTE: Unit Load is ΔI_{CC} limit specific in DC Electrical Specifications Table, e.g., 360μA max. at 25°C.

Prerequisite for Switching Specifications

PARAMETER	SYMBOL	V_{CC} (V)	25°C			-40°C TO 85°C			-55°C TO 125°C			UNITS
			MIN	TYP	MAX	MIN	TYP	MAX	MIN	TYP	MAX	
HC TYPES												
Maximum Clock Frequency	f_{MAX}	2	6	-	-	5	-	-	4	-	-	MHz
		4.5	30	-	-	25	-	-	20	-	-	MHz
		6	35	-	-	29	-	-	23	-	-	MHz
Clock Pulse Width	t_W	2	80	-	-	100	-	-	120	-	-	ns
		4.5	16	-	-	20	-	-	24	-	-	ns
		6	14	-	-	17	-	-	20	-	-	ns
Setup Time Data to Clock	t_{SU}	2	60	-	-	75	-	-	90	-	-	ns
		4.5	12	-	-	15	-	-	18	-	-	ns
		6	10	-	-	13	-	-	15	-	-	ns
Hold Time Data to Clock	t_H	2	5	-	-	5	-	-	5	-	-	ns
		4.5	5	-	-	5	-	-	5	-	-	ns
		6	5	-	-	5	-	-	5	-	-	ns
HCT TYPES												
Maximum Clock Frequency	f_{MAX}	4.5	25	-	-	20	-	-	16	-	-	MHz
Clock Pulse Width	t_W	4.5	20	-	-	25	-	-	30	-	-	ns
Setup Time Data to Clock	t_{SU}	4.5	20	-	-	25	-	-	30	-	-	ns
Hold Time Data to Clock (534)	t_H	4.5	5	-	-	5	-	-	5	-	-	ns
Hold Time Data to Clock (564)	t_H	4.5	3	-	-	3	-	-	3	-	-	ns

Switching Specifications C_L = 50pF, Input t_r, t_f = 6ns

PARAMETER	SYMBOL	TEST CONDITIONS	V_{CC} (V)	25°C			-40°C TO 85°C		-55°C TO 125°C		UNITS
				MIN	TYP	MAX	MIN	MAX	MIN	MAX	
HC TYPES											
Propagation Delay Clock to Output	t_{PLH}, t_{PHL}	C_L = 50pF	2	-	-	165	-	205	-	250	ns
			4.5	-	-	33	-	41	-	50	ns
		C_L = 15pF	5	-	13	-	-	-	-	-	ns
		C_L = 50pF	6	-	-	28	-	35	-	43	ns
Output Disable to Q (534)	t_{PLZ}, t_{PHZ}	C_L = 50pF	2	-	-	150	-	190	-	225	ns
			4.5	-	-	30	-	38	-	45	ns
		C_L = 15pF	5	-	12	-	-	-	-	-	ns
		C_L = 50pF	6	-	-	26	-	33	-	38	ns

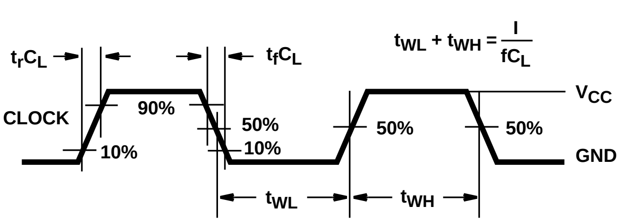
Switching Specifications C_L = 50pF, Input t_r, t_f = 6ns **(Continued)**

PARAMETER	SYMBOL	TEST CONDITIONS	V_{CC} (V)	25°C			-40°C TO 85°C		-55°C TO 125°C		UNITS
				MIN	TYP	MAX	MIN	MAX	MIN	MAX	
Output Disable to Q (564)	t_{PLZ}, t_{PHZ}	C_L = 50pF	2	-	-	135	-	170	-	205	ns
			4.5	-	-	27	-	34	-	41	ns
		C_L = 15pF	5	-	12	-	-	-	-	-	ns
		C_L = 50pF	6	-	-	23	-	29	-	35	ns
Output Enable to Q	t_{PZL}, t_{PZH}	C_L = 50pF	2	-	-	150	-	190	-	225	ns
			4.5	-	-	30	-	38	-	45	ns
		C_L = 15pF	5	-	12	-	-	-	-	-	ns
		C_L = 50pF	6	-	-	26	-	33	-	38	ns
Maximum Clock Frequency	f_{MAX}	C_L = 15pF	5	-	60	-	-	-	-	-	MHz
Output Transition Time	t_{THL}, t_{TLH}	C_L = 50pF	2	-	-	60	-	75	-	90	ns
			4.5	-	-	12	-	15	-	18	ns
			6	-	-	10	-	13	-	15	ns
Input Capacitance	C_I	C_L = 50pF	-	10	-	10	-	10	-	10	pF
Three-State Output Capacitance	C_O	-	-	20	-	20	-	20	-	20	pF
Power Dissipation Capacitance (Notes 3, 4)	C_{PD}	-	5	-	32	-	-	-	-	-	pF
HCT TYPES											
Propagation Delay Clock to Output	t_{PHL}, t_{PLH}	C_L = 50pF	4.5	-	-	35	-	44	-	53	ns
		C_L = 15pF	5	-	14	-	-	-	-	-	ns
Output Disable to Q	t_{PLZ}, t_{PHZ}	C_L = 50pF	4.5	-	-	30	-	38	-	45	ns
		C_L = 15pF	5	-	12	-	-	-	-	-	ns
Output Enable to Q	t_{PZL}, t_{PZH}	C_L = 50pF	4.5	-	-	35	-	44	-	53	ns
		C_L = 15pF	5	-	14	-	-	-	-	-	ns
Maximum Clock Frequency	f_{MAX}	C_L = 15pF	5	-	50	-	-	-	-	-	MHz
Output Transition Time	t_{TLH}, t_{THL}	C_L = 50pF	4.5	-	-	12	-	15	-	18	ns
Input Capacitance	C_I	C_L = 50pF	-	10	-	10	-	10	-	10	pF
Three-State Output Capacitance	C_O	-	-	20	-	20	-	20	-	20	pF
Power Dissipation Capacitance (Notes 3, 4)	C_{PD}	-	5	-	36	-	-	-	-	-	pF

NOTES:

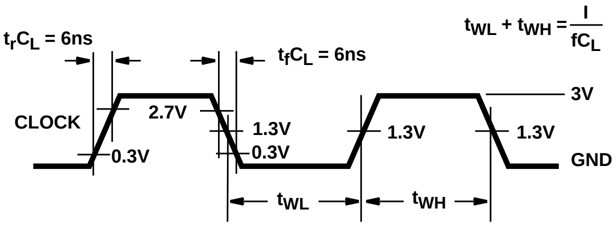
3. C_{PD} is used to determine the dynamic power consumption, per package.
4. $P_D = C_{PD} V_{CC}^2 f_i + \Sigma C_L V_{CC}^2 f_O$ where f_i = Input Frequency, f_O = Output Frequency, C_L = Output Load Capacitance, V_{CC} = Supply Voltage.

Test Circuits and Waveforms



NOTE: Outputs should be switching from 10% V_{CC} to 90% V_{CC} in accordance with device truth table. For f_{MAX}, input duty cycle = 50%.

FIGURE 1. HC CLOCK PULSE RISE AND FALL TIMES AND PULSE WIDTH



NOTE: Outputs should be switching from 10% V_{CC} to 90% V_{CC} in accordance with device truth table. For f_{MAX}, input duty cycle = 50%.

FIGURE 2. HCT CLOCK PULSE RISE AND FALL TIMES AND PULSE WIDTH

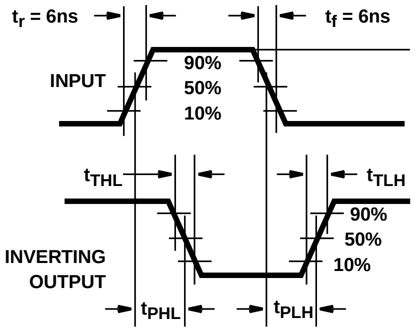


FIGURE 3. HC TRANSITION TIMES AND PROPAGATION DELAY TIMES, COMBINATION LOGIC

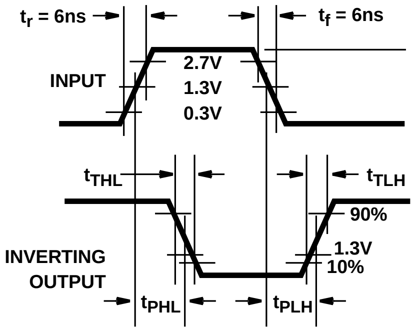


FIGURE 4. HCT TRANSITION TIMES AND PROPAGATION DELAY TIMES, COMBINATION LOGIC

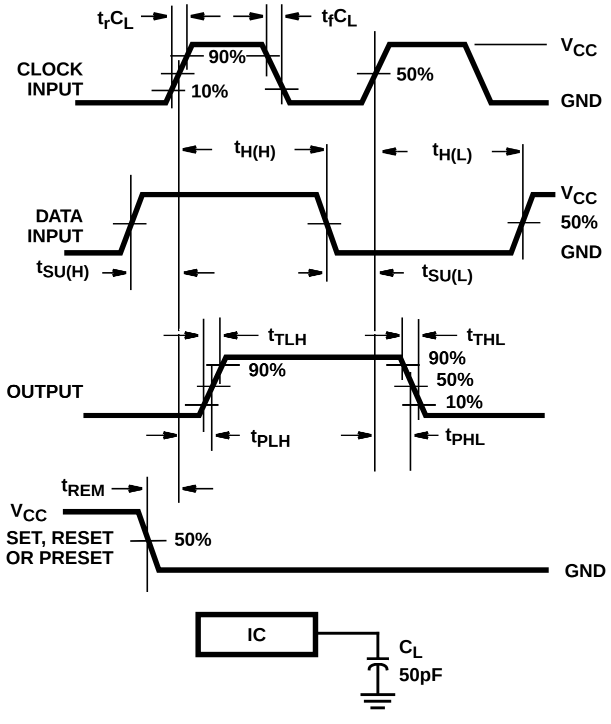


FIGURE 5. HC SETUP TIMES, HOLD TIMES, REMOVAL TIME, AND PROPAGATION DELAY TIMES FOR EDGE TRIGGERED SEQUENTIAL LOGIC CIRCUITS

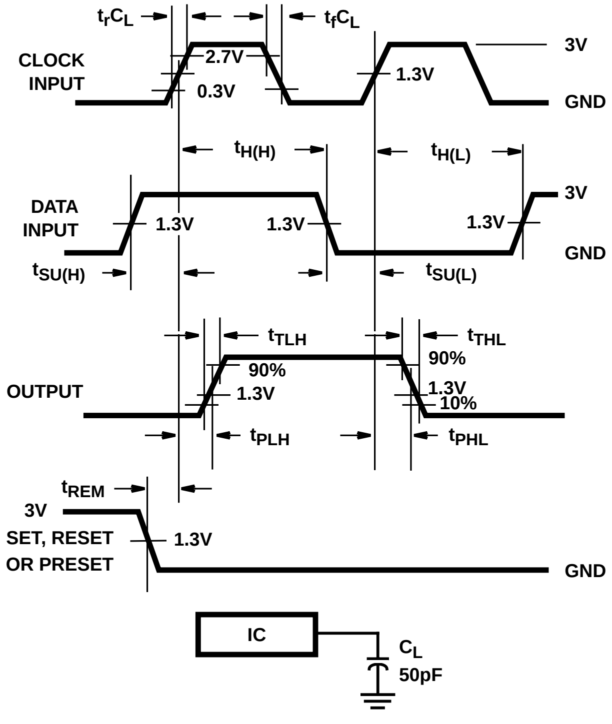


FIGURE 6. HCT SETUP TIMES, HOLD TIMES, REMOVAL TIME, AND PROPAGATION DELAY TIMES FOR EDGE TRIGGERED SEQUENTIAL LOGIC CIRCUITS

Test Circuits and Waveforms (Continued)

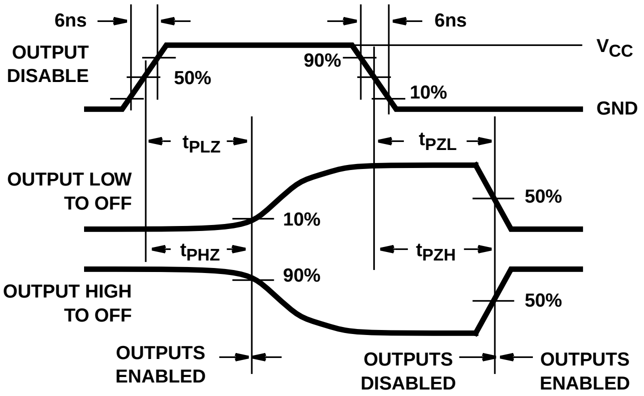


FIGURE 7. HC THREE-STATE PROPAGATION DELAY WAVEFORM

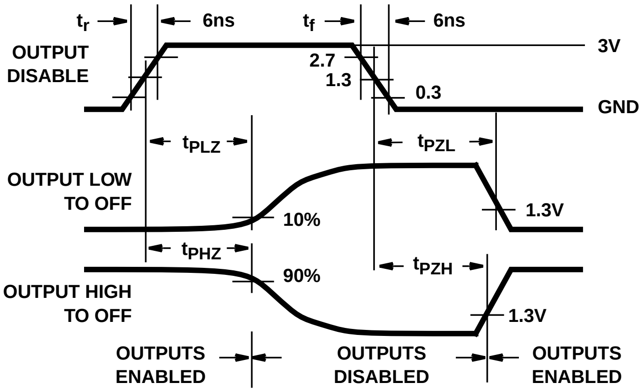
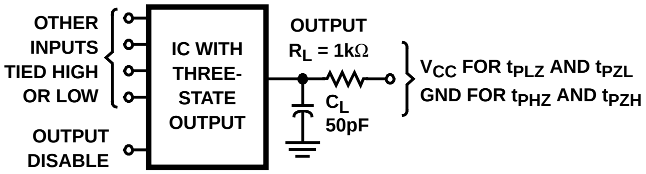


FIGURE 8. HCT THREE-STATE PROPAGATION DELAY WAVEFORM



NOTE: Open drain waveforms t_{PLZ} and t_{PZL} are the same as those for three-state shown on the left. The test circuit is Output $R_L = 1k\Omega$ to V_{CC}, $C_L = 50pF$.

FIGURE 9. HC AND HCT THREE-STATE PROPAGATION DELAY TEST CIRCUIT